

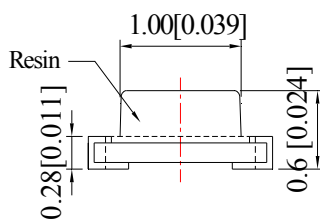
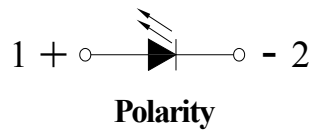
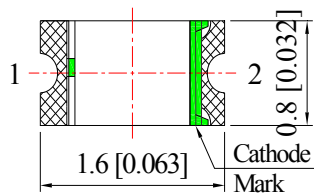
Features:

- Package in 8mm tape on 7" diameter reel.
- Compatible with automatic placement equipment.
- Compatible with infrared and vapor phase reflow solder process.
- Mono-color type.

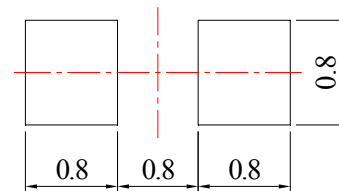
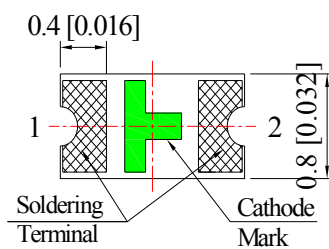
Applications:

- Backlighting in dashboard and switch.
- Telecommunication: Indicator and backlighting in telephone and fax.
- Flat backlight for LCD, switch and symbol.
- General use.

Part No.	Emitting Color	Lens Color(LED)
RND 135-00182	Super Bright Yellow	Water Clear



Recommended Soldering Pad Dimensions



Unit: mm
 Tolerance: ± 0.10 mm

Absolute Maximum Ratings at Ta=25°C

Parameters	Symbol	Max	Unit
Power Dissipation	Pd	60	mW
Peak Forward Current ^(a)	IFP	100	mA
DC Forward Current ^(b)	IF	25	mA
Reverse Voltage	VR	5	V
Electrostatic Discharge (HBM)	ESD	2000	V
Operating Temperature Range	Topr	-40°C to +80°C	
Storage Temperature Range	Tstg	-40°C to +85°C	
Soldering Temperature	Tsld	260°C for 5 Seconds	

Notes:

- a. Derate linearly as shown in derating curve.
- b. Duty Factor = 10%, Frequency = 1 kHz

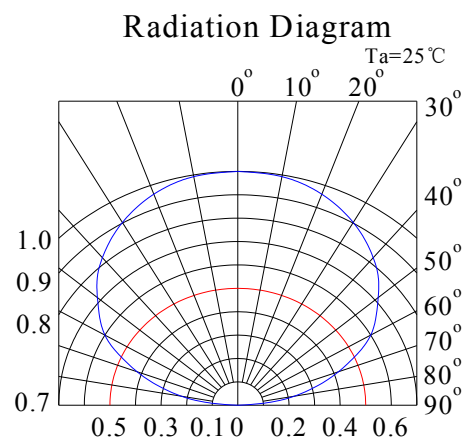
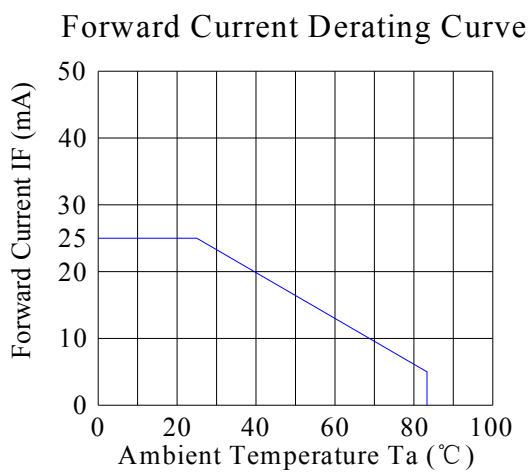
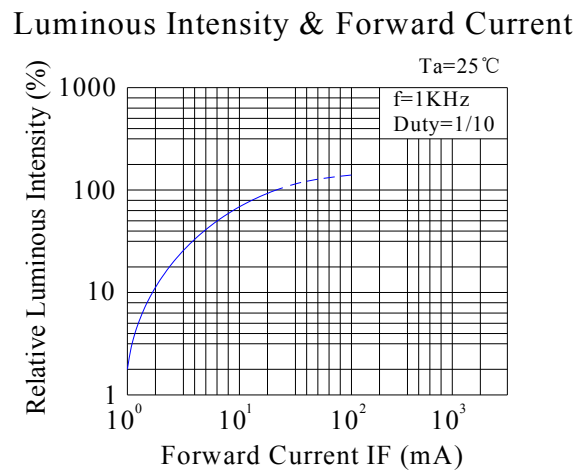
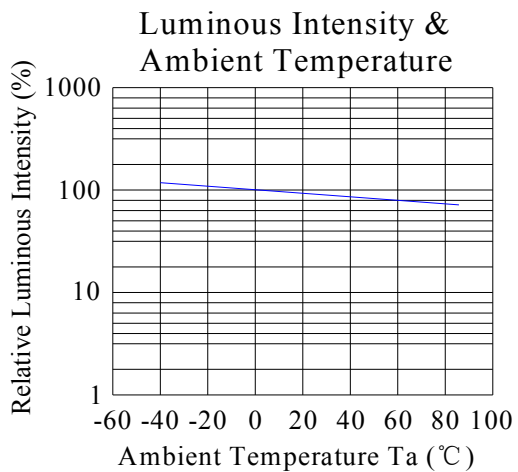
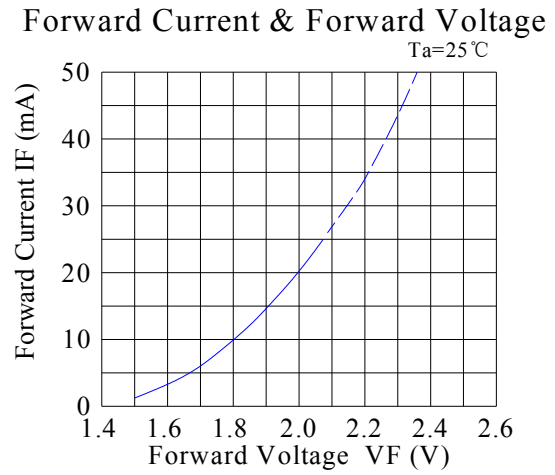
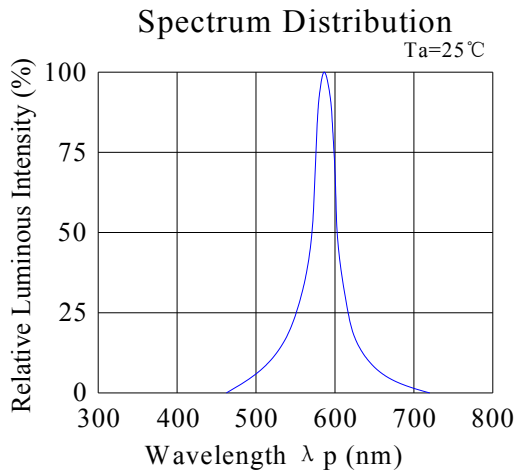
Electrical Optical Characteristics at Ta=25°C

Parameters	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Luminous Intensity ^(a)	IV	80	120	---	mcd	IF=20mA
Viewing Angle ^(b)	2θ1/2	---	130	---	Deg	IF=20mA
Peak Emission Wavelength	λp	---	592	---	nm	IF=20mA
Dominant Wavelength ^(c)	λd	---	590	---	nm	IF=20mA
Spectral Line Half-Width	Δλ	---	15	---	nm	IF=20mA
Forward Voltage	VF	1.60	2.00	2.40	V	IF=20mA
Reverse Current	IR	---	---	10	μA	VR=5V

Notes:

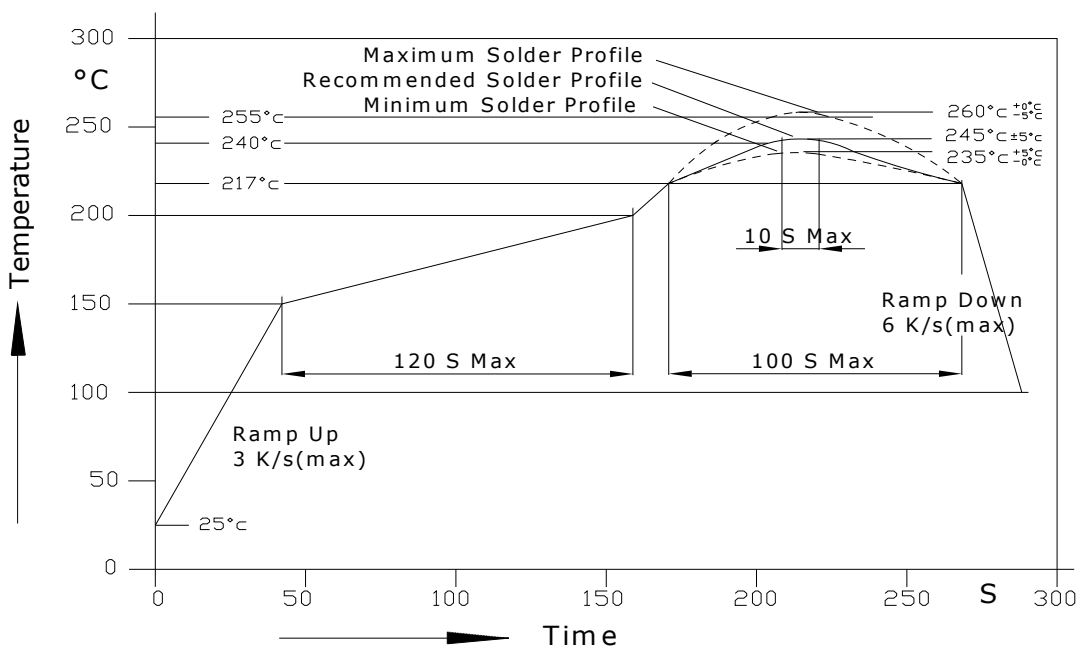
- a. ALuminous intensity is measured with a light sensor and filter combination that approximates the CIE eye-response curve.
- b. 2θ1/2 is the o -axis angle where the luminous intensity is 1/2 the peak intensity
- c. The dominant wavelength (λd) is derived from the CIE chromaticity diagram and represents the single wavelength which defines the color of the device.

Typical Electrical / Optical Characteristics Curves (25°C Ambient Temperature Unless Otherwise Noted)



Soldering Condition

Pb-free solder temperature profile



- Reflow soldering should not be done more than two times.
- When soldering, do not put stress on the LEDs during heating.
- After soldering, do not warp the circuit board.
- Recommended soldering conditions:

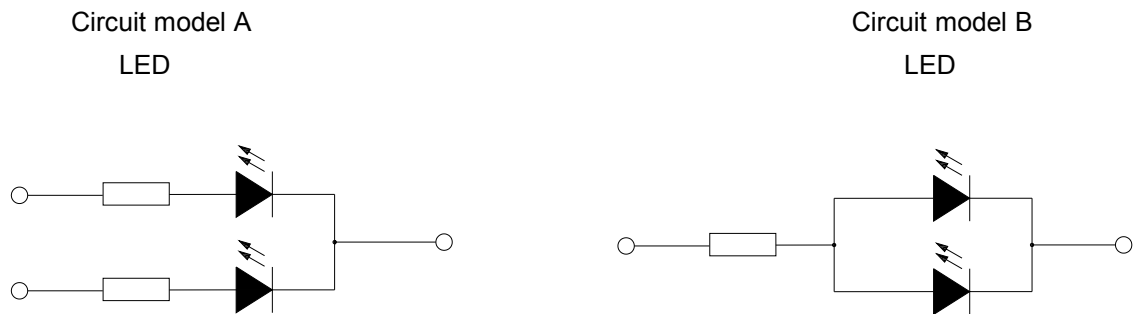
Reflow soldering		Soldering iron	
Pre-heat	150~200°C	Temperature	300°C Max.
Pre-heat time	120 sec. Max.	Soldering time	3 sec. Max.
Peak temperature	260°C Max.		(one time only)
Soldering time	10 sec. Max.(Max. two times)		

Because different board designs use different number and types of devices, solder pastes, reflow ovens, and circuit boards, no single temperature profile works for all possible combinations.

However, you can successfully mount your packages to the PCB by following the proper guidelines and PCB-specific characterization.

Drive Method

An LED is a current-operated device. In order to ensure intensity uniformity on multiple LEDs connected in parallel in an application, it is recommended that a current limiting resistor be incorporated in the drive circuit, in series with each LED as shown in Circuit A below.



a. Recommended circuit.

b. The brightness of each LED might appear different due to the differences in the I-V characteristics of those LEDs.

ESD (Electrostatic Discharge):

- Use of a conductive wrist band or anti-electrostatic glove when handling these LEDs.
- All devices, equipment, and machinery must be properly grounded.
- Work tables, storage racks, etc. should be properly grounded.
- Use ion blower to neutralize the static charge which might have built up on surface of the LED's plastic lens as a result of friction between LEDs during storage and handling.

ESD-damaged LEDs will exhibit abnormal characteristics such as high reverse leakage current, low forward voltage, or “no lightup” at low currents. To verify for ESD damage, check for “lightup” and V_f of the suspect LEDs at low currents. The V_f of “good” LEDs should be $>2.0V@0.1mA$ for InGaN product and $>1.4V@0.1mA$ for AlInGaP product.